Diplete – ET (OLD SCHEME)

Code: DE06 Time: 3 Hours

JUNE 2010

Subject: BASIC ELECTRONICS Max. Marks: 100

N	OIE: There are 9 Questions in all.
•	Question 1 is compulsory and carries
	answer book supplied and nowhere

- s 20 marks. Answer to Q.1 must be written in the space provided for it in the answer book supplied and nowhere else.
- Out of the remaining EIGHT Questions, answer any FIVE Questions. Each question carries 16 marks.
- Any required data not explicitly given, may be suitably assumed and stated.

0.1	Choose the	correct or the	best alternative	in the	following:
V.1	Choose the	correct or the	Dest ancinative	III tiit	TOHO WHIE.

 (2×10)

- a. Respective resistance values and wattage ratings of wire wound resistors are . .
 - (A) from 1Ω to $100 k\Omega$ and 400 W
 - **(B)** from 1Ω to 100Ω and 200 W
 - (C) from 1Ω to $1k\Omega$ and 300 W
 - **(D)** from 1Ω to $100 \,\mathrm{k}\Omega$ and $200 \,\mathrm{W}$
- b. In a semiconductor, the movement of holes is due to _____.
 - (A) movement of electrons in conduction band
 - (B) movement of holes in conduction band
 - (C) movement of holes in valence band
 - (D) movement of electrons in valence band
- c. In a P-N junction, the barrier Potential offers opposition to only _____.
 - (A) holes in P-region
 - **(B)** free electrons in N-region
 - (C) majority carriers in both regions
 - (**D**) minority carriers in both regions
- d. If the output voltage of a bridge rectifier is 100 V, the Peak Inverse Voltage (PIV) of diode will be ______.

(A)
$$\sqrt{2} \times 100 \text{ V}$$

(B)
$$\frac{2\times100}{\pi}$$
 \

(D)
$$\frac{\pi}{2} \times 100 \text{ V}$$

- Which of the following diodes show the negative resistance region?
 - (A) P-N junction

(B) Zener

(C) Tunnel

- (D) Schottky
- f. In an N-P-N transistor collector current is _____.
 - (A) more than emitter current

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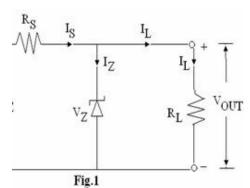
		(B) less than emitter curren(C) exactly equal to emitter(D) approximately equal to	current	•	of emitter current					
	g. In a JFET, drain current will be maximum when gate-source voltage is									
		(A) equal to ^V P	(D)	magitir ra						
		(C) negative		positive zero						
	h.	The triac is equivalent to	·							
		(A) two SCRs connected in								
		(B) two SCRs connected in	-	allal						
		(C) one SCR, one diode co (D) one diode, one SCR co								
	i.	An inverting op-amp has $^{ m R}$ f	$= 2 M\Omega$ and	$R_1 = 2 k\Omega$. Its scak	le factor is					
		(A) 1000	(B)	-1000						
		(C) 10^{-3}	(D)	-10^{-3}						
	j.	Ultraviolet radiation is used in	ı IC fabrication	process for	<u>_</u> .					
		(A) diffussion	(B)	masking						
		(C) isolation	(D)	metalization						
		Answe	•	Questions out of EIC estion carries 16 ma						
Q.2	a.	following:	lement? Name	e the most commonly	y used passive circuit elements. Briefly explain	the				
		(i) Paper capacitors.(ii) Mica capacitors.			(9)					
	b	. Differentiate between a c source with its parallel resist		•	. Give their graphical representations. Convert at tage source. (7)	1A				
Q.3	a.	What is a semiconductor impurity doping.	? Explain the (10)		e material from intrinsic semi-conductor by prop	er				
	b.	A specimen of germanium	at 300°K for	which the density of	f carriers is 2.5×10^{13} / cm ³ , is doped with impure	rity				
		atoms such that there is one ionized. The receptivity of de		-	m atoms. All the impurity atoms may be assum	æd				
					oped material, find the electron and whole densiti	es.				
		Given that the electron charge	ge (e) is 1.602 ×	:10 ⁻¹⁹ C.	(6)					
Q.4	a	Discuss how a depletion characteristics of P-N junction	•		and how does it vary with biasing? Draw the V	/ - I				
	b.	Determine the current flow	ing through the	e Zener diode for the	e circuit as shown in Fig.1, if $R_L = 5,000 \Omega$, in	out				

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voltage is 50 V, $R_S = 2,000 \Omega$ and output voltage is 30 V.





- Q.5 a. What is a voltage multiplier? What are its applications? Draw the circuit diagram of half-wave voltage doubler and explain its operation with input and output waveforms. (10)
 - b. A single-phase Full-Wave Rectifier uses two diodes, has the internal resistance of each being 20 Ω . The transformer rms secondary voltage from centre-tap to each end of secondary is 50 V and load resistance is 980 Ω . Find
 - (i) The mean load Current (I_{dc}) .
 - (ii) rms load Current (I_{rms}) and
 - (iii) Output efficiency (η).

- (6)
- Q.6 a. Sketch a family of CB output characteristics for an NPN transistor and indicate the Active, Cut-off, Saturation and Break-down regions. Explain the shapes of the curves qualitatively. (10)
 - b. The reverse leakage current of the transistor when connected in CB configuration is $0.2\,\mu\text{A}$ and it is $18\,\mu\text{A}$ when the same transistor is connected in CE configuration. Assume that the base current, I_B is 30 mA and find
 - (i) Collector Current (I_c).
 - (ii) Common Base d.c. Current gain (α_{dc}) and
 - (iii) Common Emitter d.c. Current gain (βdc) of the transistor.
- (6)

- Q.7 a. What is the significant difference between the construction of an Enhancement type MOSFET and a Depletion type MOSFET? Explain the operation of an N-channel Enhancement MOSFET. (10)
 - b. For an N-channel JFET, if $I_{DSS}=8.7\,\mathrm{mA}$; $V_P=-3\,\mathrm{V}$, and $V_{GS}=-1\,\mathrm{V}$. Find the values of
 - (i) Drain Current (I_D).
 - (ii) Transconductance for $V_{GS} = 0$ (g_{mo}) and
 - (iii) Transconductance (g_m).

- (6)
- Q.8 a. What are the various types of electron emissions? Explain in detail, the photoelectric emission.

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b. With neat diagrams, explain the construction, operation and characteristics of SCR. Mention its applications. (10)

- Q. 9. a. Draw the circuit diagram of differentiator using op-amp and derive an expression for its output voltage.

 (6)
 - b. Determine the output voltage for the op-amp circuit as shown in Fig.2, if $R_1 = R = 1k\Omega$, $R_f = 2k\Omega$, $V_a = +5V$, $V_b = -3V$ and $V_c = +4V$ (4)

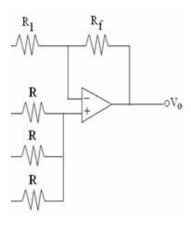


Fig.2

c. Write a short note on IC resistors.

(6)